Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π–MOSV)

# 2SK2914

# Chopper Regulator, DC-DC Converter and Moter Drive Applications

• Low drain–source ON resistance : RDS (ON) = 0.42  $\Omega$  (typ.)

• High forward transfer admittance :  $|Y_{fs}| = 7.5 \text{ S (typ.)}$ 

• Low leakage current :  $IDSS = 100 \mu A (max) (VDS = 250 V)$ 

• Enhancement-mode :  $V_{th} = 1.5 \sim 3.5 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA)}$ 

## Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	250	V	
Drain-gate voltage (R <sub>GS</sub> = 20 kΩ)		$V_{DGR}$	250	V	
Gate-source voltage		$V_{GSS}$	±20	V	
Drain current	DC (Note 1)	I <sub>D</sub>	7.5	Α	
	Pulse (Note 1)	I <sub>DP</sub>	30		
Drain power dissipatio	n (Tc = 25°C)	$P_{D}$	20	W	
Single pulse avalanche energy (Note 2)		E <sub>AS</sub>	110	mJ	
Avalanche current		I <sub>AR</sub>	7.5	Α	
Repetitive avalanche energy (Note 3)		E <sub>AR</sub>	2	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

# 10.3MAX. 03.6±0.2 10.3MAX. 03.6±0.2 OR NYWY. 1 1.6MAX. 0.76 1.6MAX. 0.76 1. GATE 2. DRAIN (HEAT SINK) 3. SOURCE JEDEC TO-220AB JEITA SC-46 TOSHIBA 2-10P1B

Weight: 2.0 g (typ.)

### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	6.25	°C/W
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	83.3	°C/W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2:  $V_{DD}$  = 50 V,  $T_{ch}$  = 25°C (initial), L = 3.3 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 7.5 A

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device.

Please handle with caution.



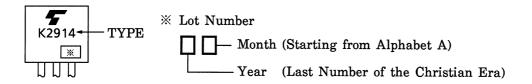
# **Electrical Characteristics (Ta = 25°C)**

Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I <sub>GSS</sub>	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0 V	_	_	±10	μΑ
Drain cut-off cu	rrent	I <sub>DSS</sub>	V <sub>DS</sub> = 250 V, V <sub>GS</sub> = 0 V	_	_	100	μΑ
Drain-source br	eakdown voltage	V (BR) DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	250	_	_	V
Gate threshold v	/oltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	1.5	_	3.5	V
Drain-source O	N resistance	R <sub>DS (ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3.5 A	_	0.42	0.5	Ω
Forward transfe	r admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3.5 A	4	7.5	_	S
Input capacitano	e	C <sub>iss</sub>			700	_	
Reverse transfe	r capacitance	C <sub>rss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	80	_	рF
Output capacita	nce	Coss		_	270	_	
Switching time -	Rise time	t <sub>r</sub>	$V_{\rm GS}$ $0$ $0$ $0$ $0$ $0$ $0$ $0$ $0$ $0$ $0$	_	10	_	
	Turn-on time	t <sub>on</sub>		_	20	_	ne
	Fall time	t <sub>f</sub>		_	10	_	ns
	Turn-off time	t <sub>off</sub>	Duty $\leq 1\%$ , $t_{\rm W} = 10 \mu \rm s$	_	70	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	20	_	
Gate-source charge		Q <sub>gs</sub>	$V_{DD} \approx 200 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 7.5 \text{ A}$		13	_	nC
Gate-drain ("miller") Charge		Q <sub>gd</sub>			7	_	

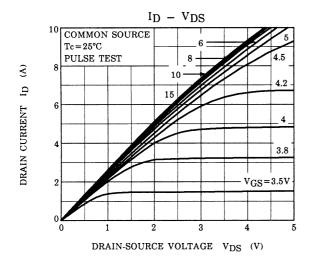
# **Source-Drain Ratings and Characteristics (Ta = 25°C)**

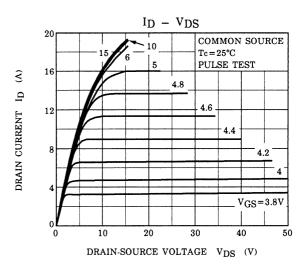
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	_	_	_	7.5	Α
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	_	_	_	30	А
Forward voltage (diode)	V <sub>DSF</sub>	I <sub>DR</sub> = 7.5 A, V <sub>GS</sub> = 0 V	_	_	-2.0	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 7.5 A, V <sub>GS</sub> = 0 V		180	_	ns
Reverse recovery charge	Qrr	dI <sub>DR</sub> / dt = 100 Å / μs	1	1.1	_	μC

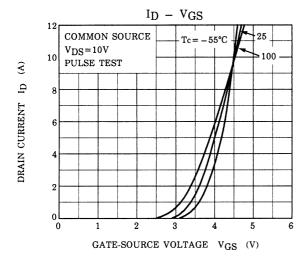
# Marking

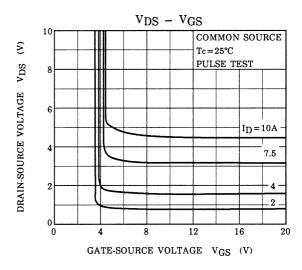


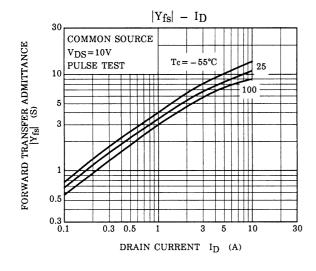
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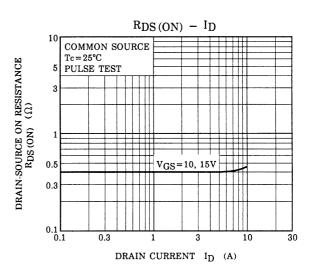




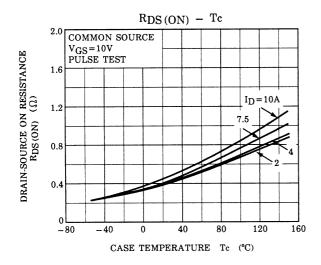


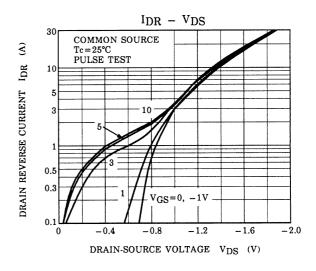


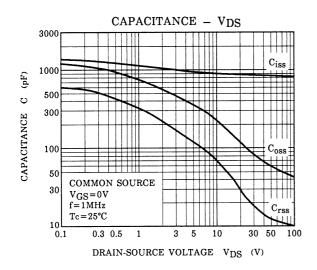


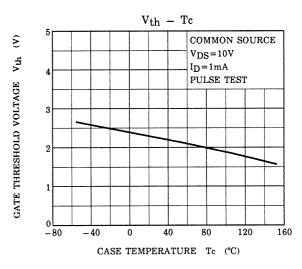


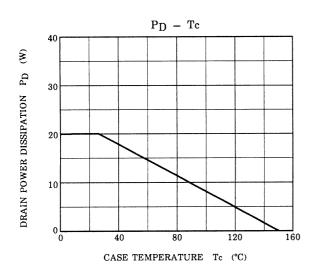
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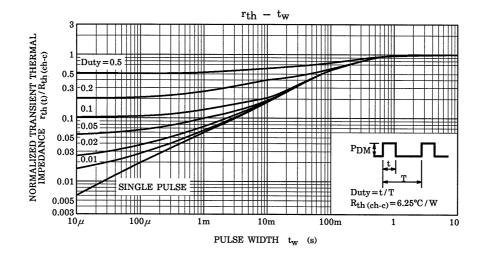


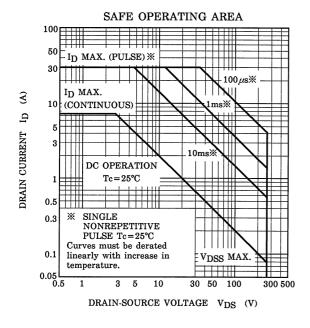


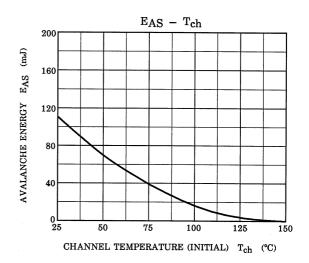


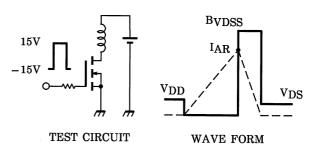


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$$R_G = 25 \Omega$$
  
 $V_{DD} = 50 \text{ V}, L = 3.3 \text{ mH}$   $E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}}\right)$ 

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